



DMPH4023SK3Q

40V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C		
-40V	26mΩ @ V _{GS} = -10V	-50A		

Features

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

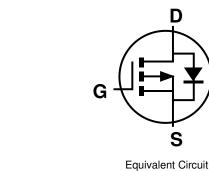
- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment



Top View

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH4023SK3Q-13	TO252 (DPAK)	2500/Tape & Reel

D

U D

Pin Out

Top View

S

G

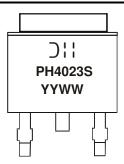
Notes:

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



) | | = Manufacturer's Marking
PH4023S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-40	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = -10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	-50 -35	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-70	А
Maximum Continuous Body Diode Forward Current (Note 7)		Is	-4	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	-70	А
Avalanche Current, L = 0.1mH (Note 8)	las	-40	А	
Avalanche Energy, L = 0.1mH (Note 8)		E _{AS}	85	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{OJA}	71	°C/W
Total Power Dissipation (Note 7)		PD	3.6	W
ermal Resistance, Junction to Ambient (Note 7) Steady State		R _{eja}	41	°C/W
Thermal Resistance, Junction to Case		R _{eJC}	1.5	-C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

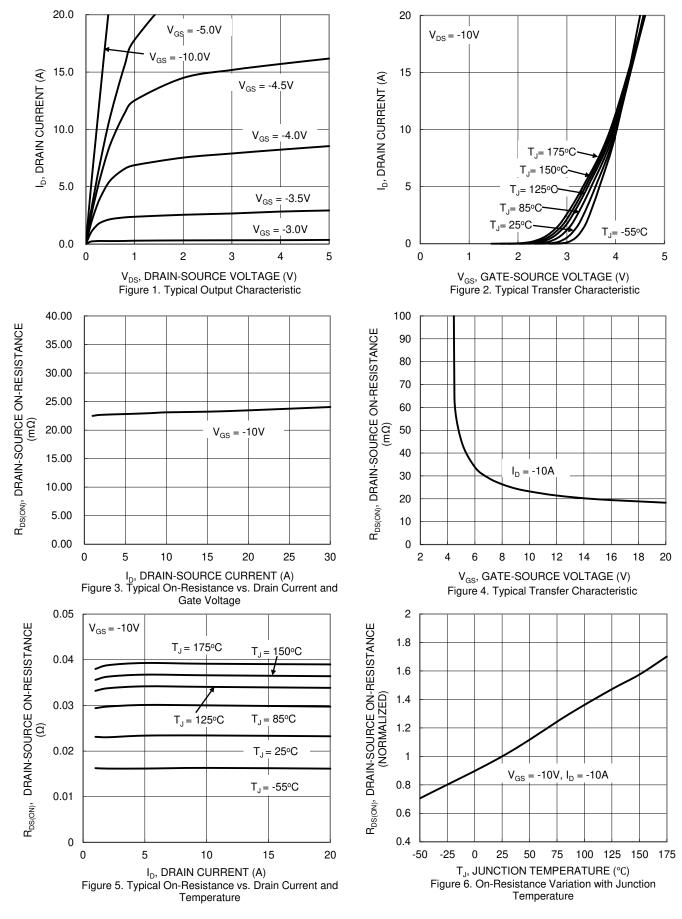
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	Тур	Wax	Unit	Test Collation	
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	+0		-1	μA	$V_{GS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_		±100	nA	$V_{\rm DS} = \pm 20V, V_{\rm DS} = 0V$ $V_{\rm GS} = \pm 20V, V_{\rm DS} = 0V$	
ON CHARACTERISTICS (Note 9)	1655			100	103	VGS = ±20V, VDS = 0V	
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	21	26	mΩ	$V_{GS} = -10V, I_D = -10A$	
Diode Forward Voltage	V _{SD}		-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)						-	
Input Capacitance	C _{iss}		1091	—	рF		
Output Capacitance	Coss	_	288	—	pF	V _{DS} = -20V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	111	_	pF		
Gate Resistance	Rg	_	14		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	18.7	_	nC	$y_{1} = 20y_{1} = 100$	
Gate-Source Charge	Q _{qs}	_	4.2		nC	$V_{DS} = -20V, I_D = -10A,$	
Gate-Drain Charge	Q _{gd}	_	5.0	_	nC	V _{GS} = -10V	
Turn-On Delay Time	t _{D(ON)}	_	5.3		ns		
Turn-On Rise Time	t _R	_	4.8	_	ns	V _{DD} = -20V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(OFF)}		30.7	_	ns	$R_G = 6\Omega, I_D = -10A$	
Turn-Off Fall Time	t _F		23.4	_	ns		
Reverse Recovery Time	t _{RR}		17.8	_	ns	L = 100 di/dt = 1000 / m c	
Reverse Recovery Charge	Q _{RR}		9.2		nC	I _F = -10A, di/dt = -100A/µs	

6. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout. Notes:

8. Device mounted on FR-4 substrate PCB, 202 copper, with minimum recommended parts 7. Device mounted on FR-4 substrate PCB, 202 copper, with 1inch square copper plate. 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.

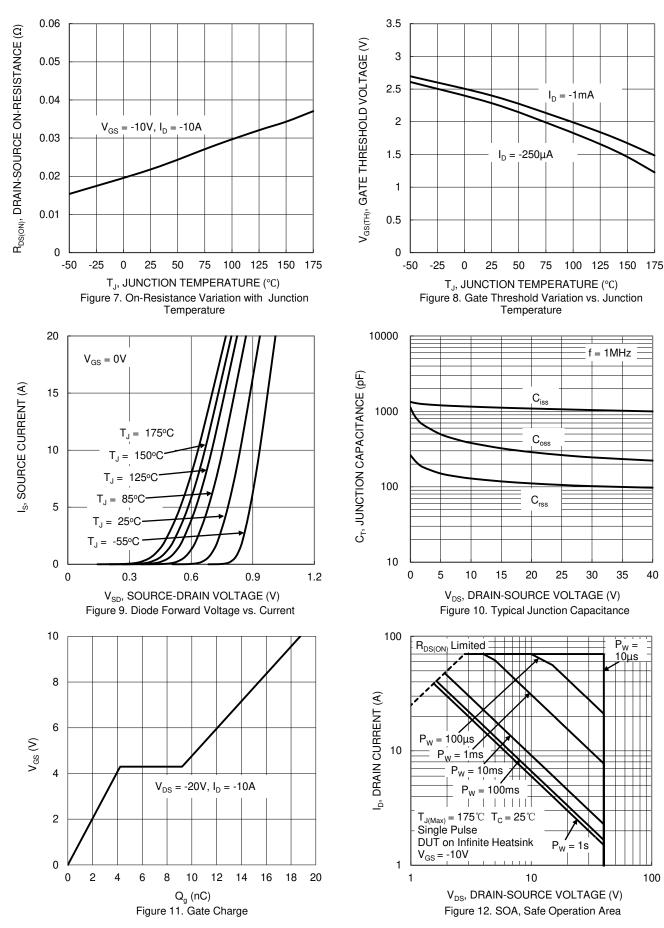


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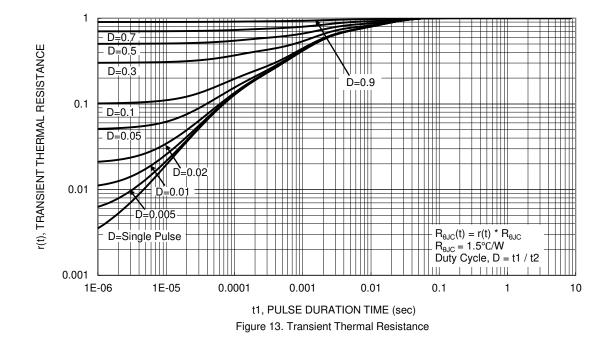
DMPH4023SK3Q Document number: DS40995 Rev. 1 - 2





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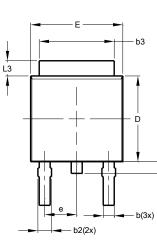


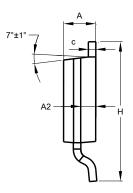


Package Outline Dimensions

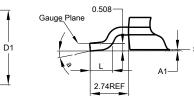
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TO252 (DPAK)

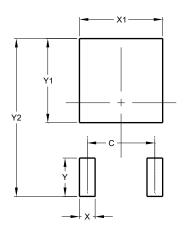


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All	All Dimensions in mm					

Suggested Pad Layout

F1

Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)

eating Plane

Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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